

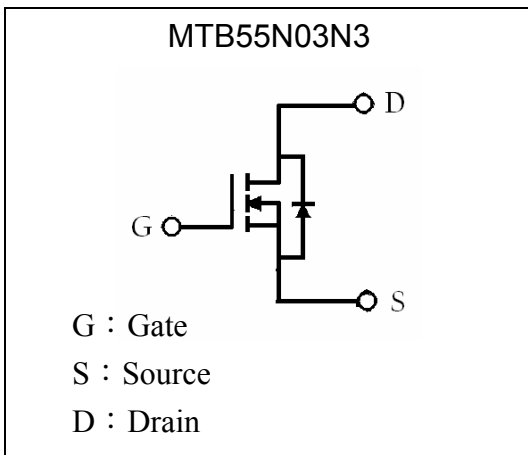
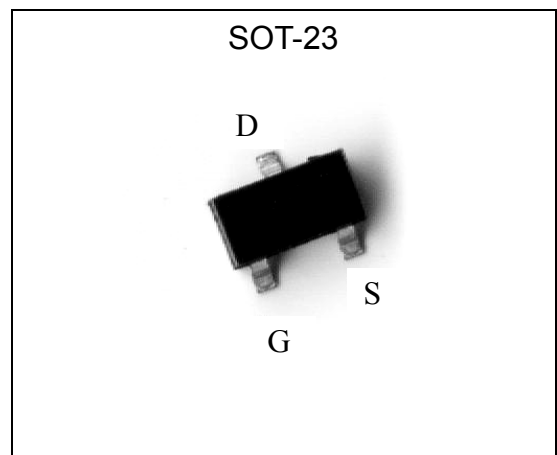
30V N-Channel Logic Level Enhancement Mode MOSFET

MTB55N03N3

BV_{DSS}	30V
I_D	4.8A
$R_{DS(on)(TYP)}@V_{GS}=10V, I_D=3.5A$	35m Ω
$R_{DS(on)(TYP)}@V_{GS}=4.5V, I_D=2A$	58m Ω

Features

- Lower gate charge
- Pb-free lead plating and Halogen-free package

Equivalent Circuit

Outline

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}, V_{GS}=10\text{V}$	4.8
		$T_A=70^\circ\text{C}, V_{GS}=10\text{V}$	3.8
Pulsed Drain Current	I_{DM}	20 (Note 1 & 2)	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	1.38 (Note 3)
		$T_A=70^\circ\text{C}$	0.88 (Note 3)
Thermal Resistance, Junction to Ambient	$R_{th, j-a}$	90 (Note 3)	$^\circ\text{C/W}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55 ~ +150	$^\circ\text{C}$

Note : 1. Pulse width limited by maximum junction temperature.

 2. Duty cycle $\leq 1\%$.

 3. Surface mounted on 1 in² copper pad of FR4 board, $\leq 10\text{s}$; 270 $^\circ\text{C/W}$ when mounted on min. copper pad.



Electrical Characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	30	-	-	V	$V_{GS}=0, I_D=250\mu\text{A}$
$V_{GS(th)}$	1	1.8	3	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0$
I_{DSS}	-	-	1	μA	$V_{DS}=24\text{V}, V_{GS}=0$
	-	-	10		$V_{DS}=20\text{V}, V_{GS}=0, T_j=125^{\circ}\text{C}$
$*R_{DS(ON)}^1$	-	35	45	m Ω	$I_D=3.5\text{A}, V_{GS}=10\text{V}$
	-	58	75		$I_D=2\text{A}, V_{GS}=4.5\text{V}$
$*G_{FS}^1$	-	5	-	S	$V_{DS}=5\text{V}, I_D=3.5\text{A}$
Dynamic					
C_{iss}	-	384	-	pF	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$
C_{oss}	-	46	-		
C_{rSS}	-	34	-		
$*t_{d(ON)}^{1\ 2}$	-	4	-	ns	$V_{DS}=10\text{V}, I_D=1\text{A}, V_{GS}=10\text{V}, R_G=6\Omega$
$*t_r^{1\ 2}$	-	3.7	-		
$*t_{d(OFF)}^{1\ 2}$	-	8	-		
$*t_f^{1\ 2}$	-	3.5	-		
$*Q_g^{1\ 2}$	-	6	-	nC	$V_{DS}=10\text{V}, I_D=4.8\text{A}, V_{GS}=4.5\text{V}$
$*Q_{gs}^{1\ 2}$	-	1.5	-		
$*Q_{gd}^{1\ 2}$	-	1.7	-		
Source-Drain Diode					
I_S	-	-	2	A	
I_{SM}^3	-	-	8		
V_{SD}^1	-	0.85	1.2	V	$I_F=I_S, V_{GS}=0\text{V}$

¹ Pulse test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

² Independent of operating temperature

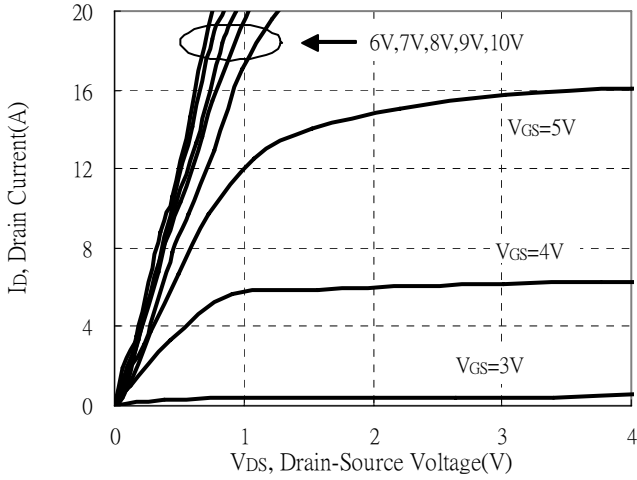
³ Pulse width limited by maximum junction temperature

Ordering Information

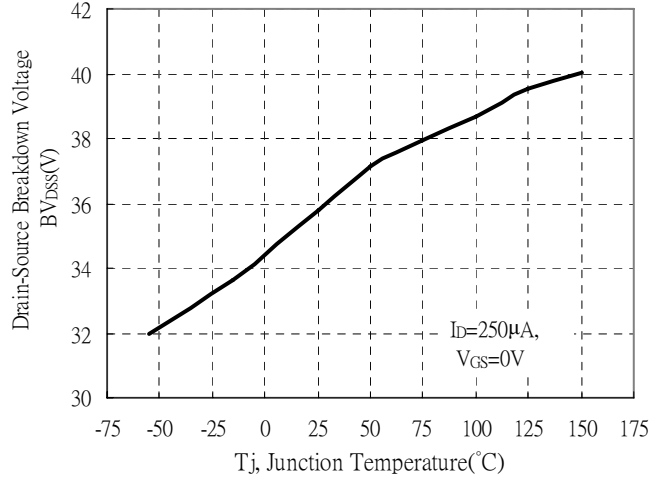
Device	Package	Shipping
MTB55N03N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Typical Characteristics

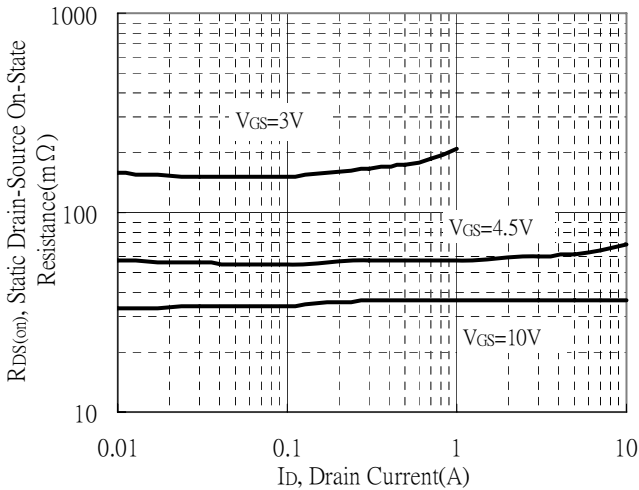
Typical Output Characteristics



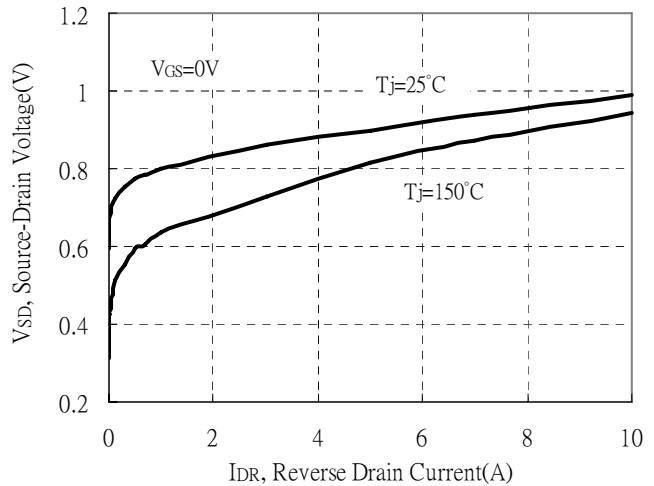
Brekdown Voltage vs Ambient Temperature



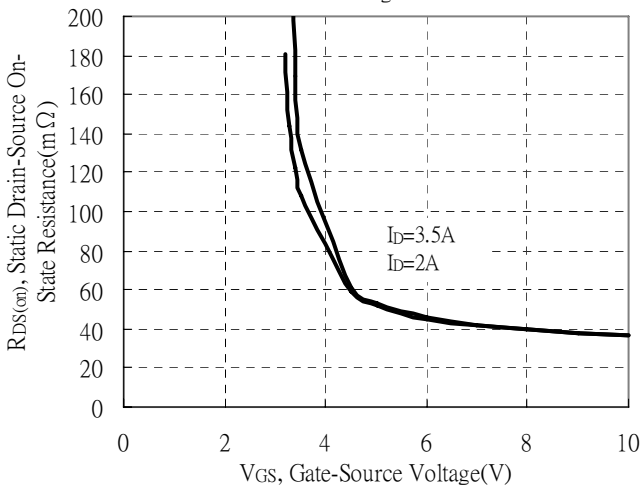
Static Drain-Source On-State resistance vs Drain Current



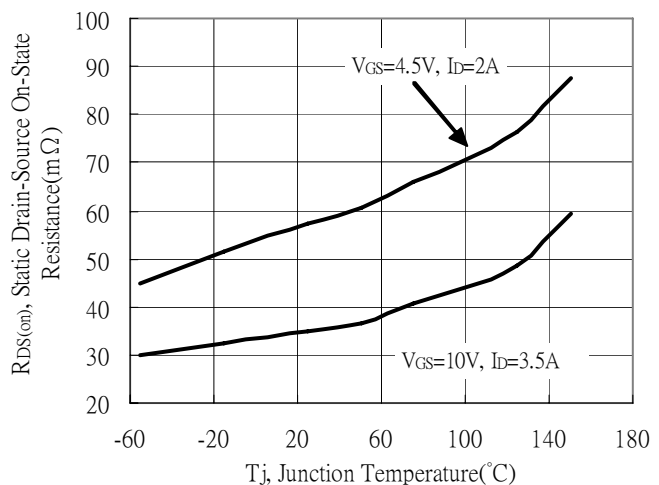
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

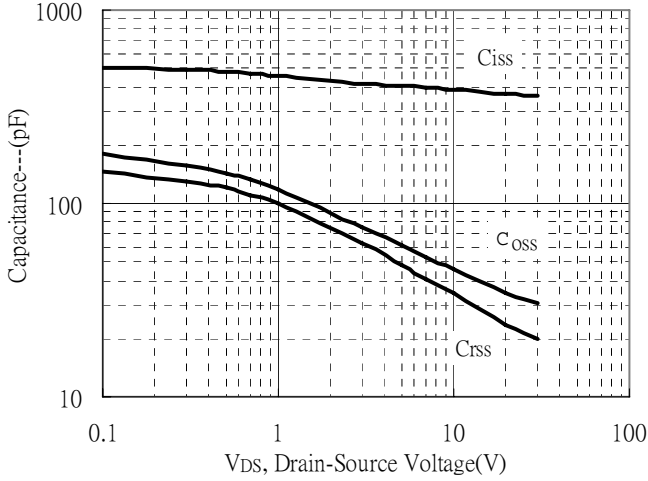


Drain-Source On-State Resistance vs Junction Temperature

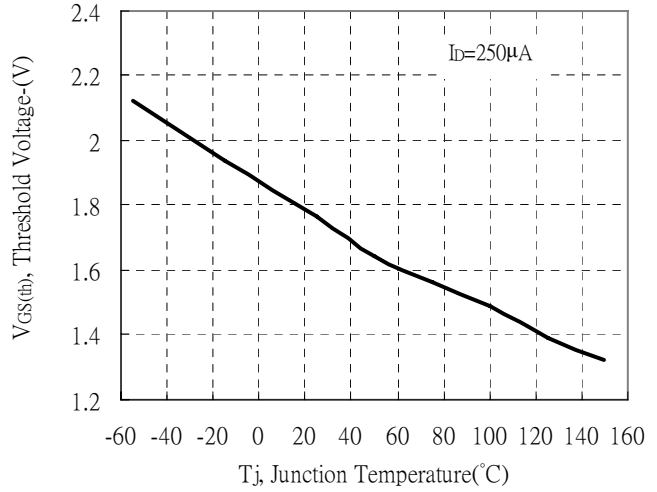


Typical Characteristics(Cont.)

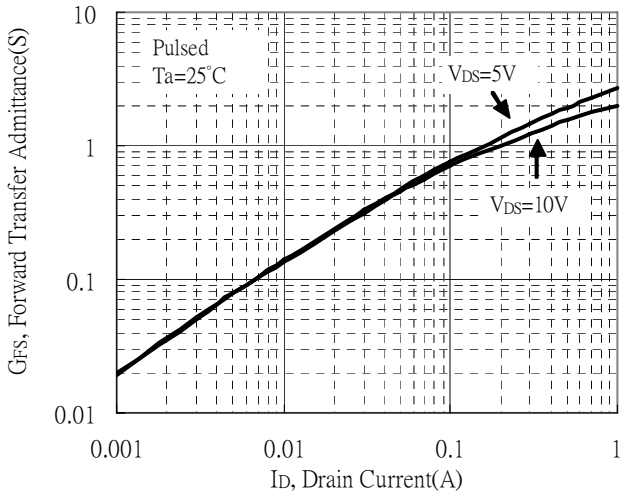
Capacitance vs Drain-to-Source Voltage



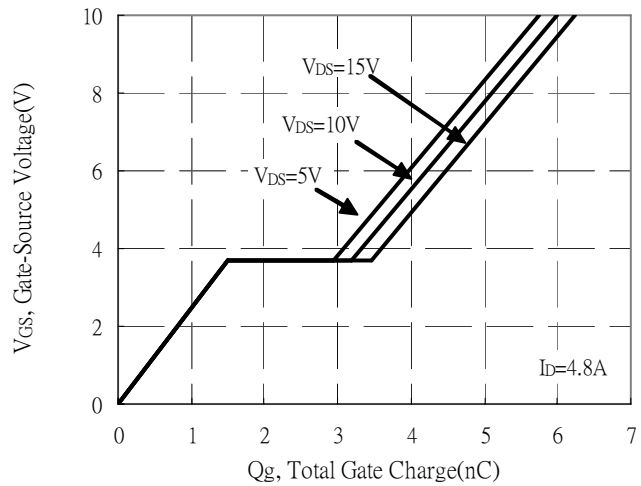
Threshold Voltage vs Junction Temperature



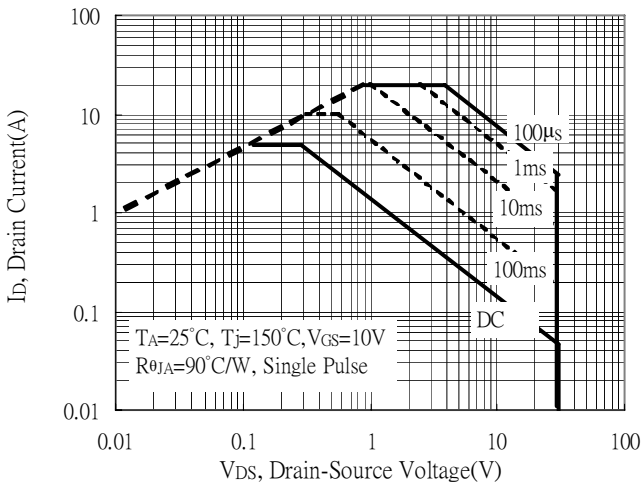
Forward Transfer Admittance vs Drain Current



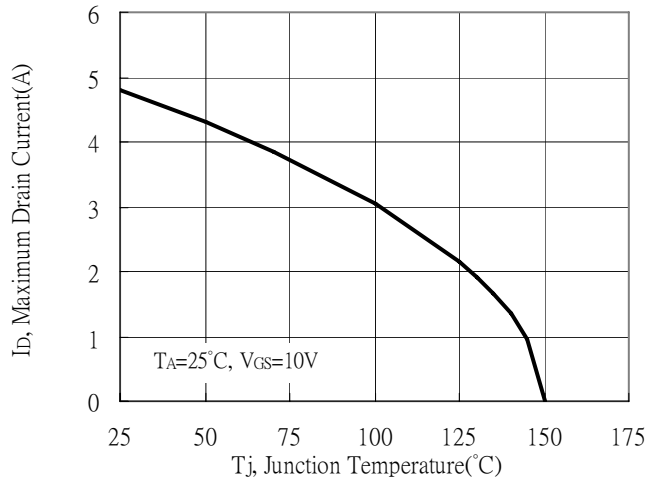
Gate Charge Characteristics



Maximum Safe Operating Area

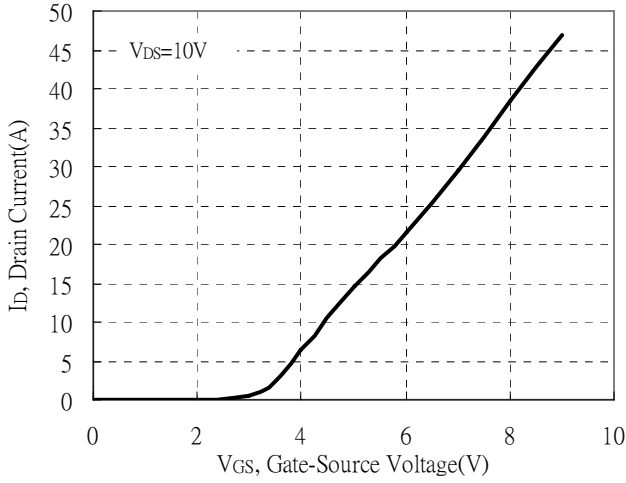


Maximum Drain Current vs Junction Temperature

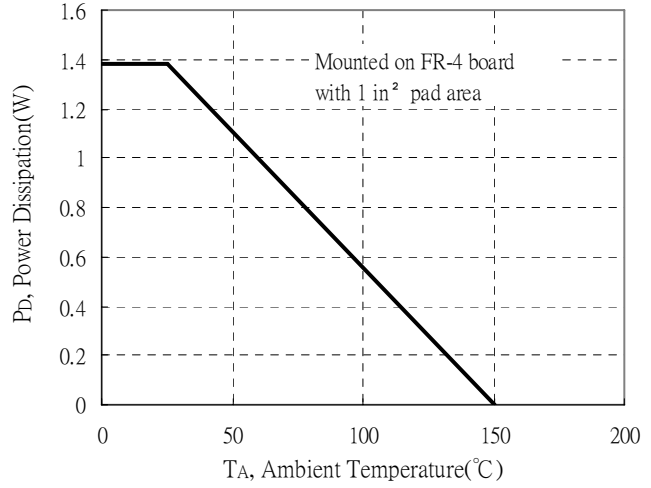


Typical Characteristics(Cont.)

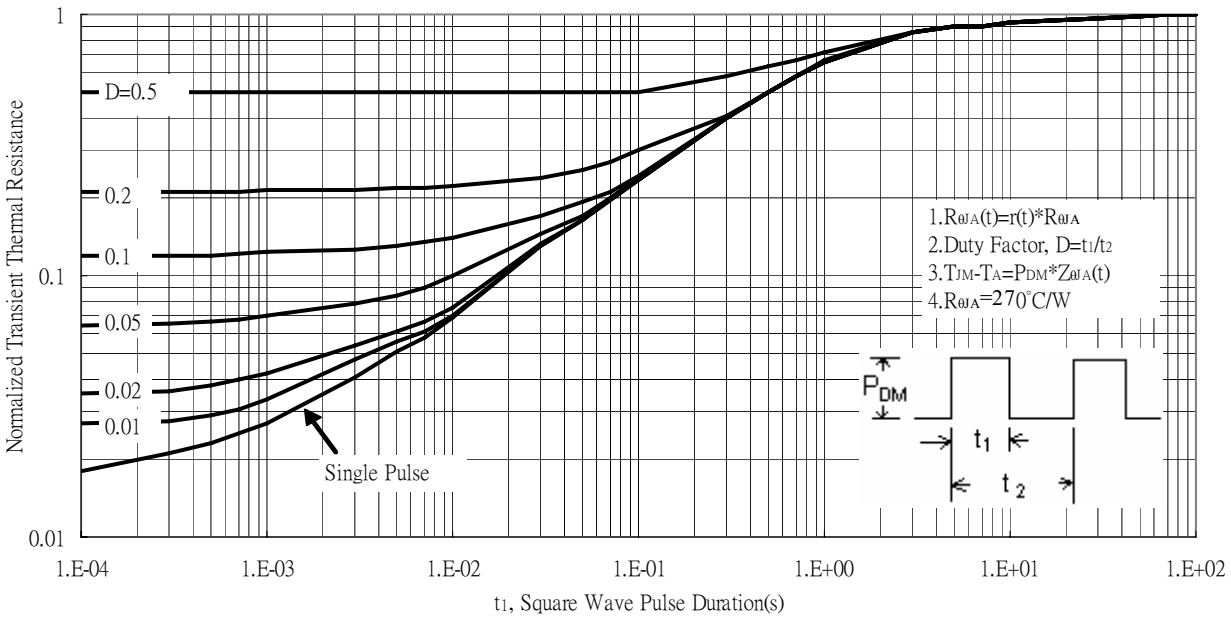
Typical Transfer Characteristics



Power Derating Curve

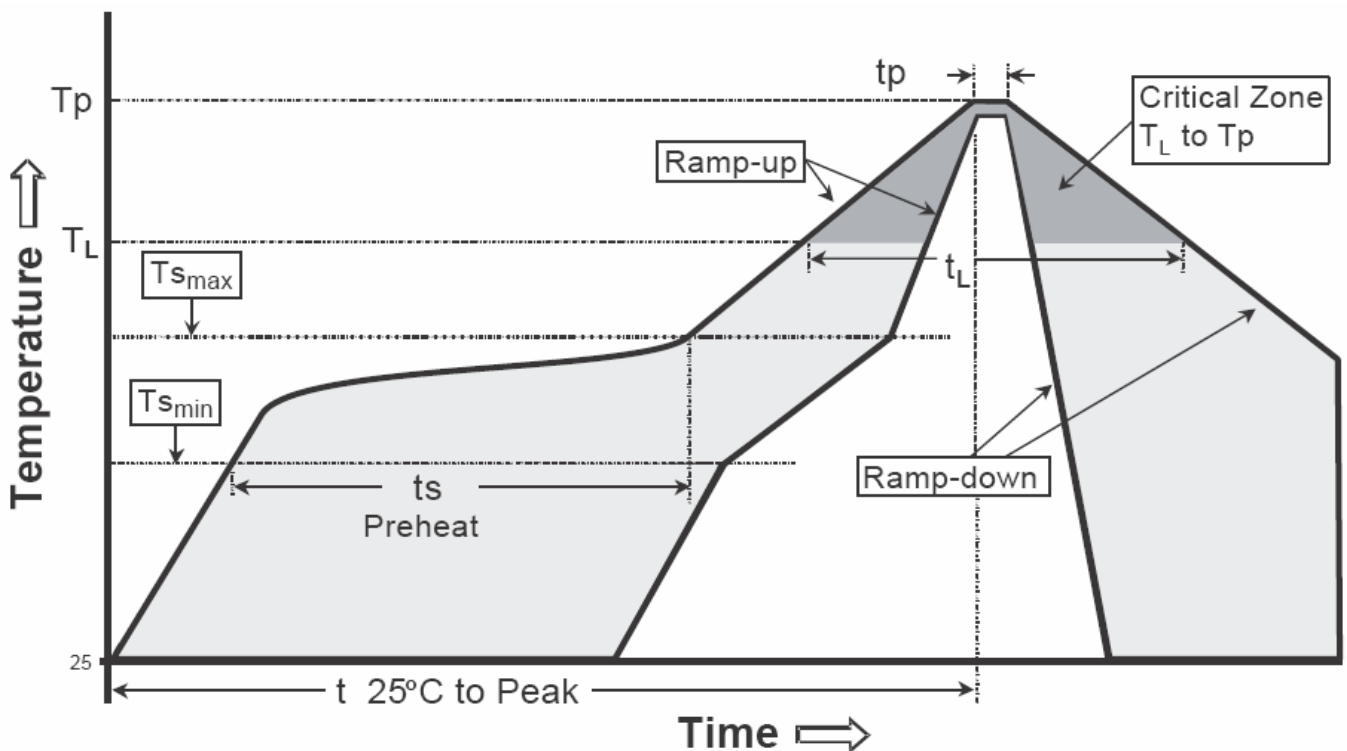


Transient Thermal Response Curves



Recommended wave soldering condition

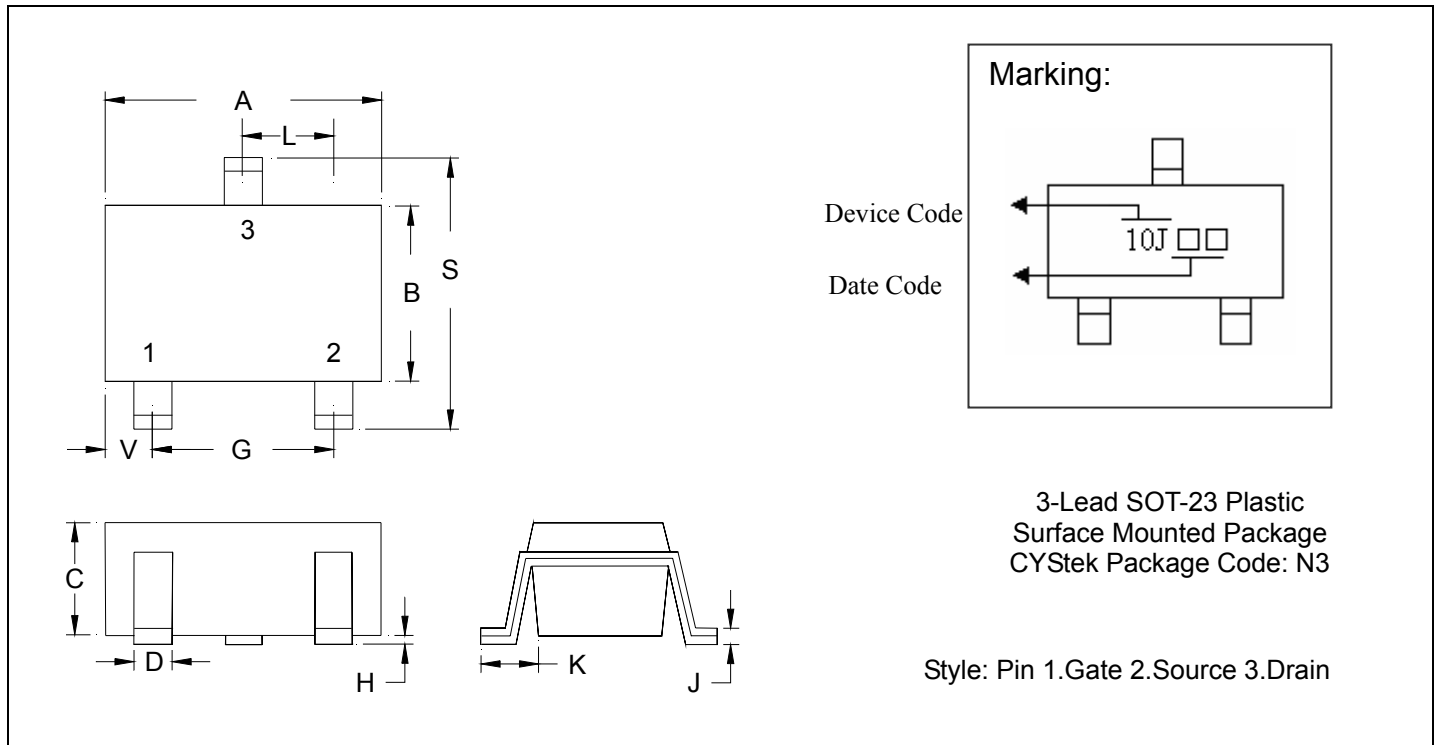
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

- Notes:**
- Controlling dimension: millimeters.
 - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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